

Product Summary

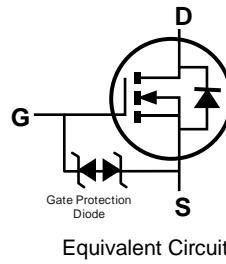
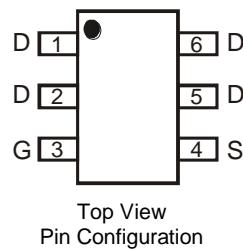
| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | I_D $T_A = +25^\circ\text{C}$ |
|---------------|---------------------------------------|------------------------------------|
| 12V | 10m Ω @ $V_{GS} = 4.5\text{V}$ | 10.7A |
| | 12m Ω @ $V_{GS} = 2.5\text{V}$ | 9.8A |
| | 14m Ω @ $V_{GS} = 1.8\text{V}$ | 9.1A |
| | 18m Ω @ $V_{GS} = 1.5\text{V}$ | 8.0A |
| | 41m Ω @ $V_{GS} = 1.2\text{V}$ | 5.3A |

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters
- Power Management Functions



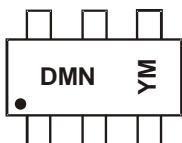
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|--------|--------------------|
| DMN1019UVT-7 | TSOT26 | 3,000/Tape & Reel |
| DMN1019UVT-13 | TSOT26 | 10,000/Tape & Reel |

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DMN = Product Type Marking Code
 YM or YM = Date Code Marking
 Y or Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | | | | |
|-------|------|------|------|------|------|------|------|------|-----|-----|-----|-----|
| Code | C | D | E | F | G | H | I | J | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|--|------------------|--|-----------|--------------|-------|
| Drain-Source Voltage | | | V_{DSS} | 12 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 8 | V |
| Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 10.7 8.6 | A |
| | $t < 10\text{s}$ | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 12.7 10.1 | A |
| Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%) | | | I_{DM} | 70 | A |
| Maximum Body Diode Forward Current (Note 5) | | | I_S | 2 | A |
| Avalanche Current (Note 6) $L = 0.1\text{mH}$ | | | I_{AS} | 9.7 | A |
| Avalanche Energy (Note 6) $L = 0.1\text{mH}$ | | | E_{AS} | 4.7 | mJ |

Thermal Characteristics

| Characteristic | | | Symbol | Value | Units | |
|--|------------------|---------------------------|-----------------|--------------------|--------------------|--|
| Total Power Dissipation (Note 5) | | $T_A = +25^\circ\text{C}$ | P_D | 1.73 | W | |
| | | $T_A = +70^\circ\text{C}$ | | 1.11 | | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{\theta JA}$ | 72.2 | $^\circ\text{C/W}$ | | |
| | $t < 10\text{s}$ | | 37.5 | $^\circ\text{C/W}$ | | |
| Thermal Resistance, Junction to Case (Note 5) | | | $R_{\theta JC}$ | 14.4 | $^\circ\text{C/W}$ | |
| Operating and Storage Temperature Range | | | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ | |

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|--------------|------|-------|---------|------------------|---|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 12 | — | — | V | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | — | — | 1 | μA | $V_{DS} = 12\text{V}, V_{GS} = 0\text{V}$ |
| Gate-Body Leakage | I_{GSS} | — | — | ± 2 | μA | $V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$ |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 0.35 | 0.53 | 0.8 | V | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 7 | 10 | $\text{m}\Omega$ | $V_{GS} = 4.5\text{V}, I_D = 9.7\text{A}$ |
| | | — | 8 | 12 | | $V_{GS} = 2.5\text{V}, I_D = 9\text{A}$ |
| | | — | 10 | 14 | | $V_{GS} = 1.8\text{V}, I_D = 8.1\text{A}$ |
| | | — | 14 | 18 | | $V_{GS} = 1.5\text{V}, I_D = 4.5\text{A}$ |
| | | — | 28 | 41 | | $V_{GS} = 1.2\text{V}, I_D = 2.4\text{A}$ |
| Diode Forward Voltage | V_{SD} | — | 0.8 | 1.2 | V | $V_{GS} = 0\text{V}, I_S = 10\text{A}$ |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C_{iss} | — | 2588 | — | pF | $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ |
| Output Capacitance | C_{oss} | — | 415 | — | pF | |
| Reverse Transfer Capacitance | C_{rss} | — | 394 | — | pF | |
| Gate Resistance | R_g | — | 1.1 | — | Ω | $V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ |
| Total Gate Charge ($V_{GS} = 8\text{V}$) | Q_g | — | 50.4 | — | nC | $V_{DS} = 4\text{V}, I_D = 10\text{A}$ |
| Total Gate Charge ($V_{GS} = 4.5\text{V}$) | Q_g | — | 28.0 | — | | |
| Gate-Source Charge | Q_{gs} | — | 3.2 | — | | |
| Gate-Drain Charge | Q_{gd} | — | 5.6 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 4.7 | — | ns | $V_{DD} = 4\text{V}, V_{GEN} = 5\text{V}, I_D = 10\text{A}, R_G = 1\Omega, R_L = 0.4\Omega$ |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 32.2 | — | ns | |
| Turn-On Rise Time | t_R | — | 3.7 | — | ns | |
| Turn-Off Fall Time | t_F | — | 11.6 | — | ns | |
| Body Diode Reverse Recovery Time | t_{RR} | — | 20.55 | — | ns | $I_F = 10\text{A}, di/dt = 100\text{A}/\mu\text{s}$ |
| Body Diode Reverse Recovery Charge | Q_{rr} | — | 4.5 | — | nC | $I_F = 10\text{A}, di/dt = 100\text{A}/\mu\text{s}$ |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad.

6. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

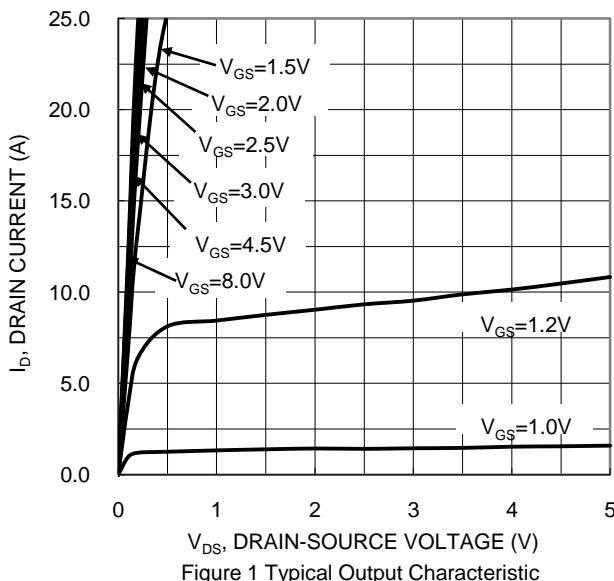


Figure 1 Typical Output Characteristic

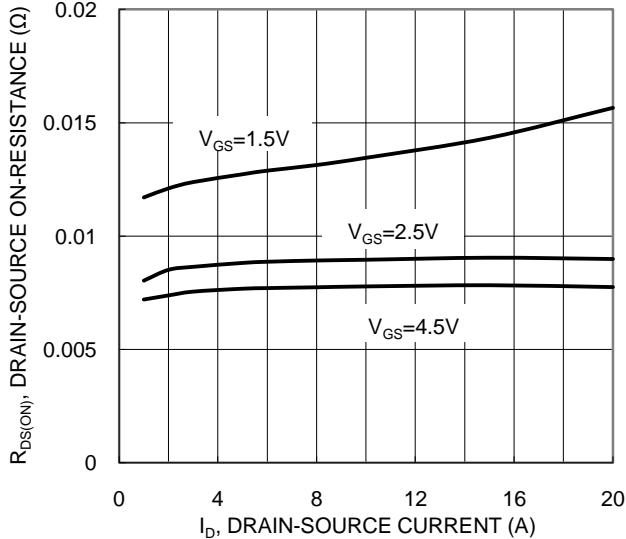


Figure 3 Typical On-Resistance vs Drain Current and Gate Voltage

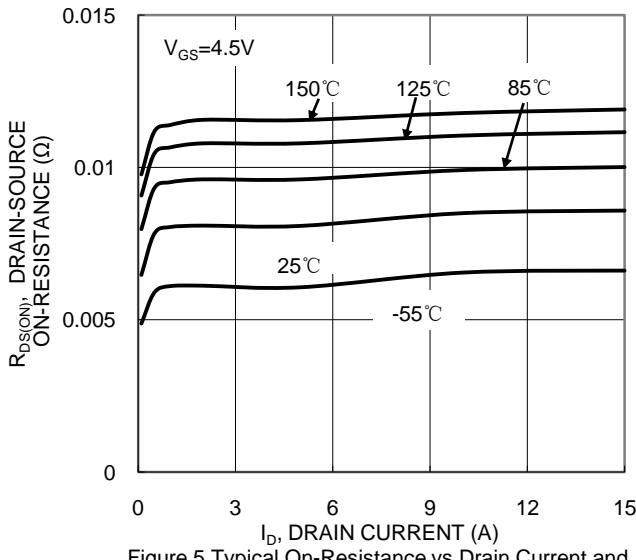


Figure 5 Typical On-Resistance vs Drain Current and Temperature

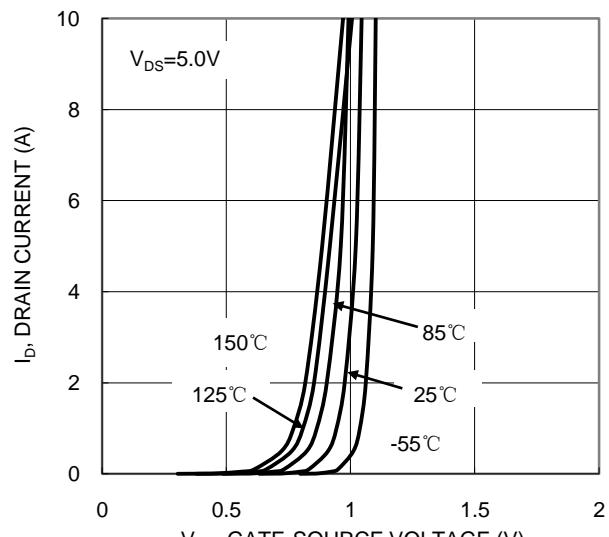


Figure 2 Typical Transfer Characteristic

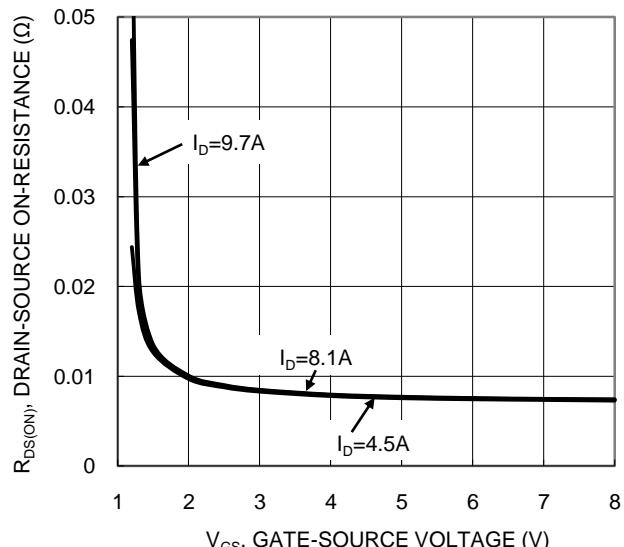


Figure 4 Typical On-Resistance vs Drain Current and Gate Voltage

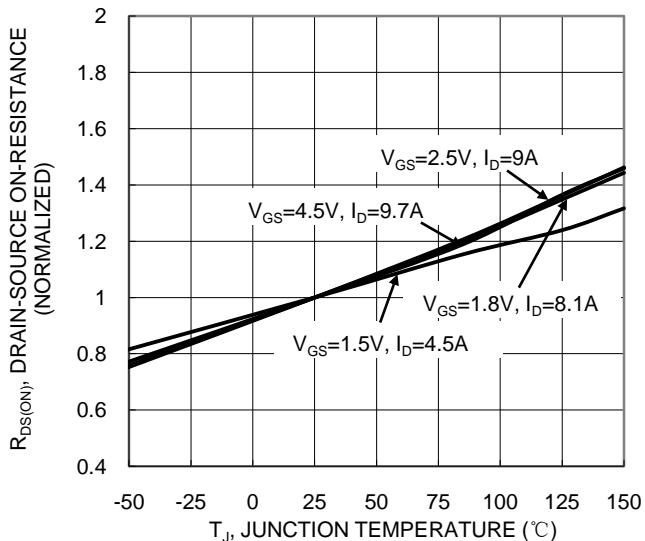


Figure 6 On-Resistance Variation with Temperature

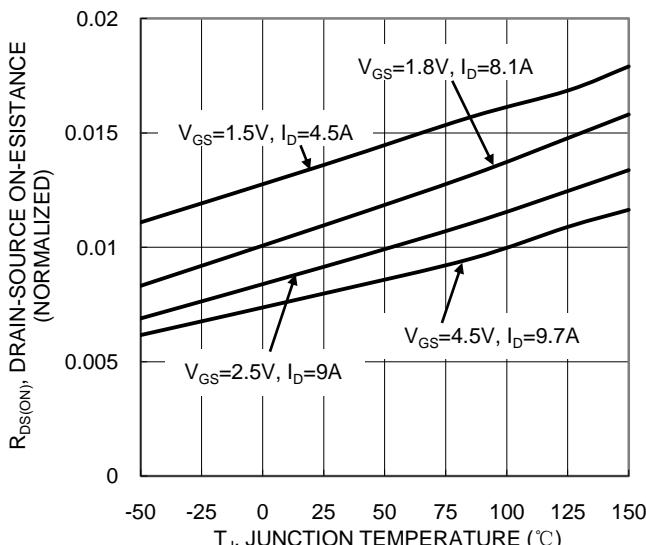


Figure 7 On-Resistance Variation with Temperature

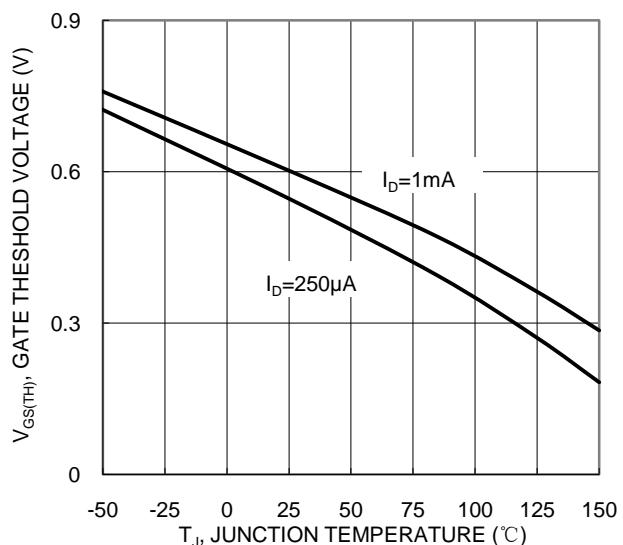


Figure 8 Gate Threshold Variation vs Junction Temperature

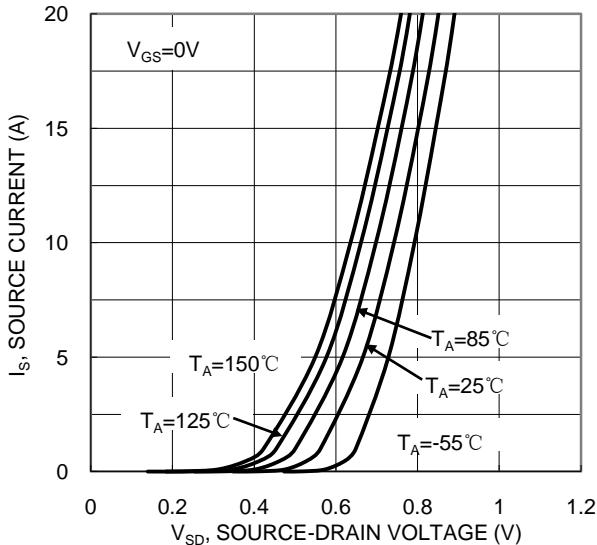


Figure 9 Diode Forward Voltage vs Current

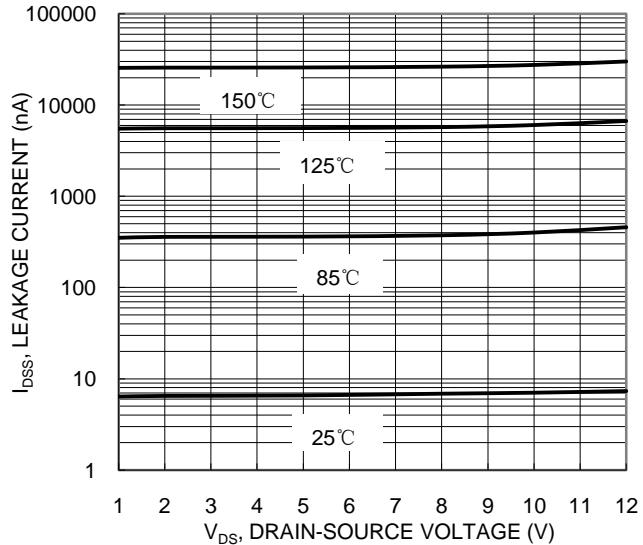


Figure 10 Typical Drain-Source Leakage Current vs Voltage

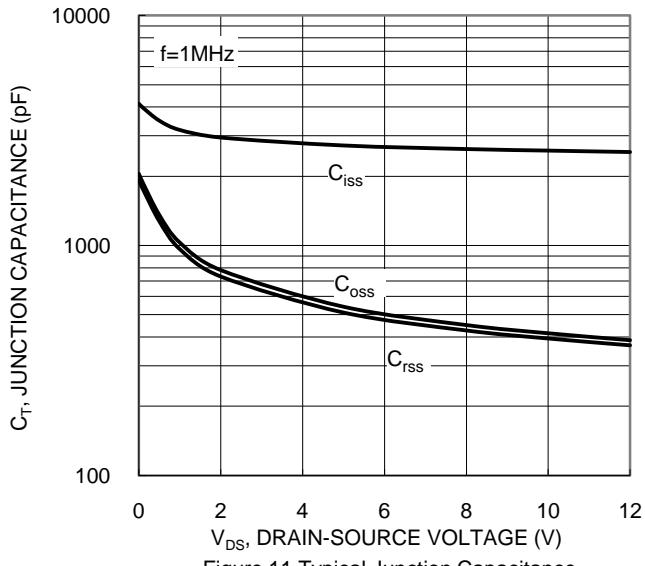


Figure 11 Typical Junction Capacitance

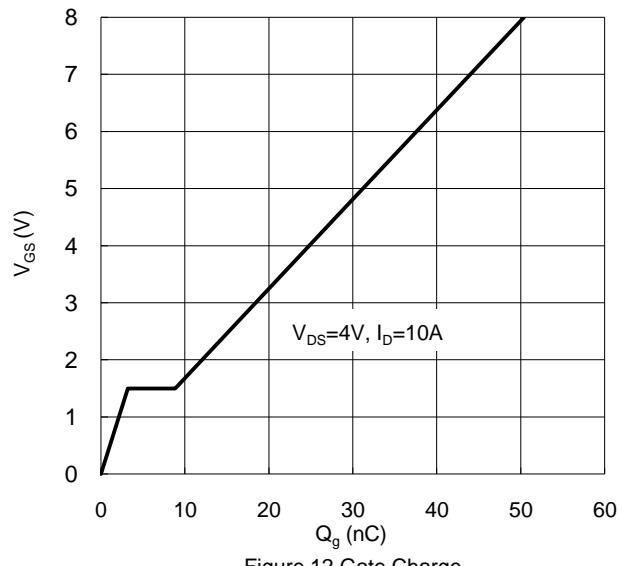


Figure 12 Gate Charge

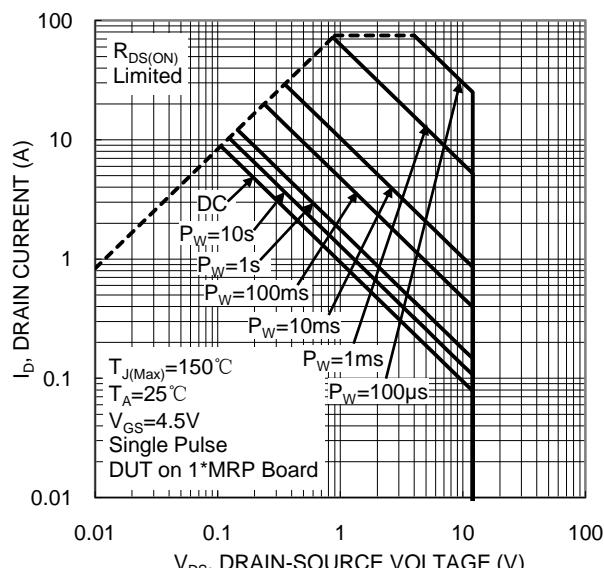


Figure 13 SOA, Safe Operation Area

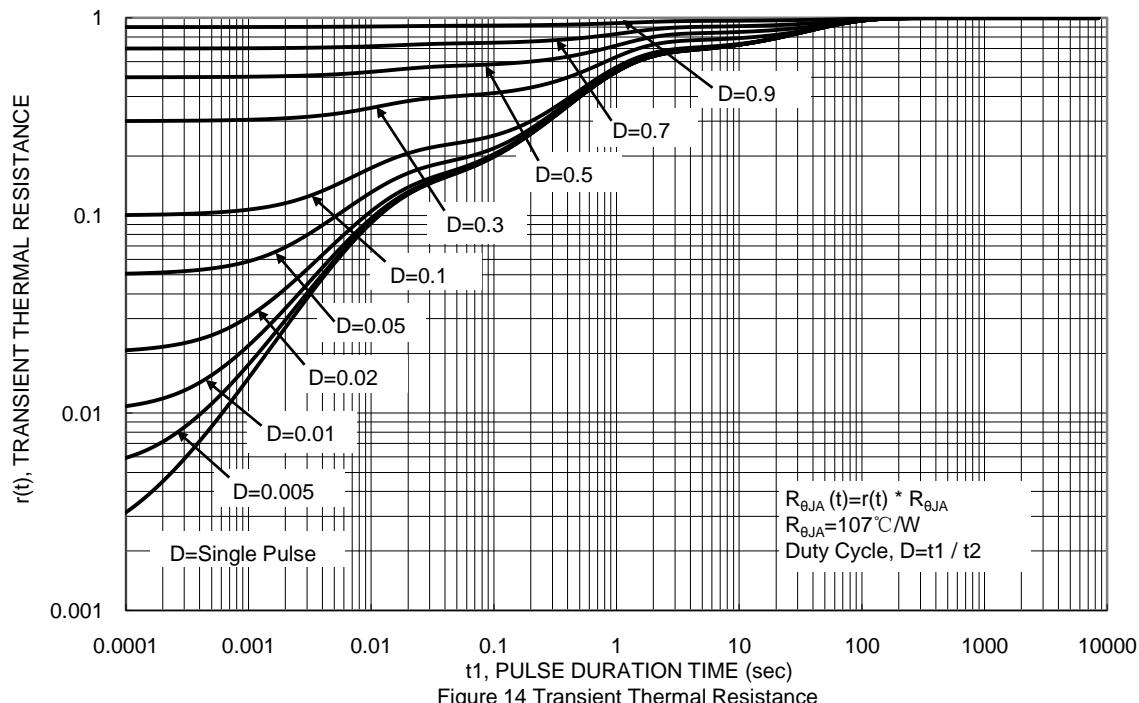
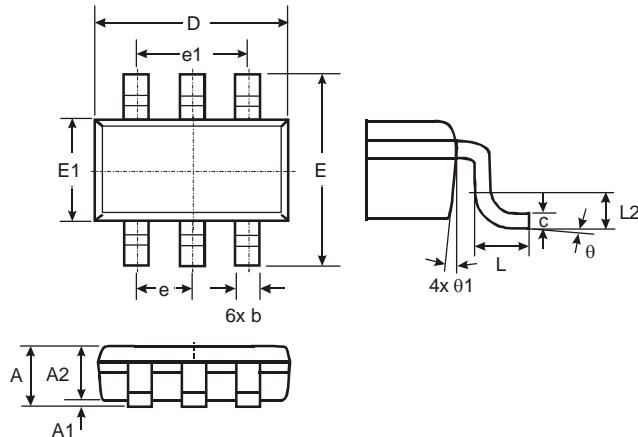


Figure 14 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

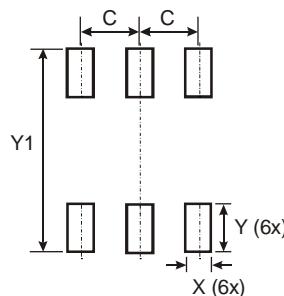


| TSOT26 | | | |
|-----------|------|------|------|
| Dim | Min | Max | Typ |
| A | — | 1.00 | — |
| A1 | 0.01 | 0.10 | — |
| A2 | 0.84 | 0.90 | — |
| D | — | — | 2.90 |
| E | — | — | 2.80 |
| E1 | — | — | 1.60 |
| b | 0.30 | 0.45 | — |
| c | 0.12 | 0.20 | — |
| e | — | — | 0.95 |
| e1 | — | — | 1.90 |
| L | 0.30 | 0.50 | — |
| L2 | — | — | 0.25 |
| θ | 0° | 8° | 4° |
| θ1 | 4° | 12° | — |

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.950 |
| X | 0.700 |
| Y | 1.000 |
| Y1 | 3.199 |

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